## Shubhadeep Bhattacharjee

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5178198/publications.pdf

Version: 2024-02-01

21 papers 438 citations

11 h-index 18 g-index

21 all docs

21 docs citations

21 times ranked

565 citing authors

#	Article	IF	CITATIONS
1	Interfacial ferroelectricity in marginally twisted 2D semiconductors. Nature Nanotechnology, 2022, 17, 390-395.	31.5	115
2	Insights into Multilevel Resistive Switching in Monolayer MoS <sub>2</sub> . ACS Applied Materials & amp; Interfaces, 2020, 12, 6022-6029.	8.0	54
3	Surface State Engineering of Metal/MoS <sub>2</sub> Contacts Using Sulfur Treatment for Reduced Contact Resistance and Variability. IEEE Transactions on Electron Devices, 2016, 63, 2556-2562.	3.0	44
4	Out-of-equilibrium criticalities in graphene superlattices. Science, 2022, 375, 430-433.	12.6	34
5	A sub-thermionic MoS2 FET with tunable transport. Applied Physics Letters, 2017, 111, .	3.3	32
6	High Performance HfO2 Back Gated Multilayer MoS2 transistors. IEEE Electron Device Letters, 2016, , 1-1.	3.9	31
7	Emulating synaptic response in n- and p-channel MoS2 transistors by utilizing charge trapping dynamics. Scientific Reports, 2020, 10, 12178.	3.3	21
8	Nitride Dielectric Environments to Suppress Surface Optical Phonon Dominated Scattering in Highâ€Performance Multilayer MoS <sub>2</sub> FETs. Advanced Electronic Materials, 2017, 3, 1600358.	5.1	20
9	Intrinsic Limit for Contact Resistance in Exfoliated Multilayered MoS <sub>2</sub> FET. IEEE Electron Device Letters, 2016, 37, 119-122.	3.9	18
10	Early Detection of Breast Cancer: Synthesis and Characterization of Novel Target Specific NIR-Fluorescent Estrogen Conjugate for Molecular Optical Imaging. Journal of Fluorescence, 2011, 21, 1171-1177.	2.5	15
11	Large-area growth of MoS <sub>2</sub> at temperatures compatible with integrating back-end-of-line functionality. 2D Materials, 2021, 8, 025008.	4.4	14
12	Effects of Annealing Temperature and Ambient on Metal/PtSe <sub>2</sub> Contact Alloy Formation. ACS Omega, 2019, 4, 17487-17493.	3.5	10
13	Optical-Phonon-Limited High-Field Transport in Layered Materials. IEEE Transactions on Electron Devices, 2016, 63, 767-772.	3.0	7
14	Hole Injection and Rectifying Heterojunction Photodiodes through Vacancy Engineering in MoS 2. Advanced Electronic Materials, 2019, 5, 1800863.	5.1	7
15	Two-Dimensional Materials and Their Role in Emerging Electronic and Photonic Devices. Electrochemical Society Interface, 2018, 27, 53-58.	0.4	5
16	Gallium Selenide Nanoribbons on Silicon Substrates for Photodetection. ACS Applied Nano Materials, 2021, 4, 7820-7831.	5.0	5
17	(Invited) Interface Engineering of High-k Dielectrics and Metal Contacts for High Performance Top-Gated MoS2FETs. ECS Transactions, 2017, 80, 101-107.	0.5	3
18	Adaptive Transport in High Performance (I on), Steep Sub-Threshold Slope (SS < 60 mV/dec) MoS2 Transistors. IEEE Nanotechnology Magazine, 2019, 18, 1071-1078.	2.0	2

#	Article	IF	CITATIONS
19	Optoelectronics based on Vertical Transport in Multi-layer MoS2. , 2018, , .		1
20	Early detection of breast cancer: a molecular optical imaging approach using novel estrogen conjugate fluorescent dye. , $2011$ , , .		O
21	Realizing P-FETs and photodiodes on MoS <inf>2</inf> through area-selective p-doping via vacancy engineering. , 2017, , .		O